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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Selzer
Application No.: 09/876,443
Filing Date: June 7, 2001
Title: Method of Improving X-Ray
Lithography in the Sub 100nm
Range to Create High Quality
Semiconductor Devices

Docket No. 1520-006 (1426)
Date: May 8, 2002
Group Art Unit: 2882
Examiner: I. Kiknadze
FAX: 703 305-3594
No. of pages sent:

TERMINAL DISCLAIMER
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JUN 14 2002

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Terminal Disclaimer Under 37 CFR 1.321(c)

Applicant disclaims term of any patent granted on this application extending beyond the term of
US Patent 6,295,332.

The present application is commonly assigned with US Patent 6,295,332.

A fee sheet and the fee set forth in 37 CFR 1.20(d) is attached.

Any patent granted on the application shall be enforceable only for and during such period that
said patent is commonly owned with the patent which formed the basis for the double patenting
rejection (US Patent 6,295,332).

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Respectfully submitted,

For: Selzer et al.

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